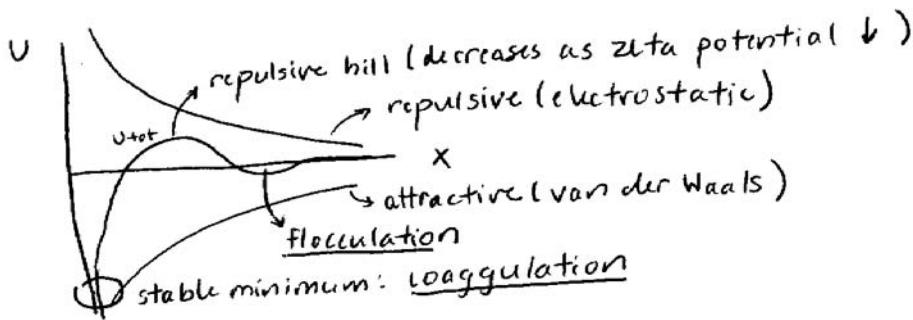
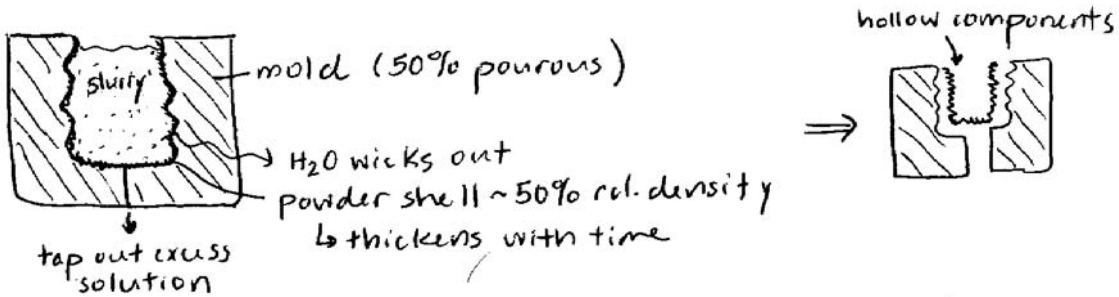


### 3.044 MATERIALS PROCESSING

#### LECTURE 22

#### Slip Casting



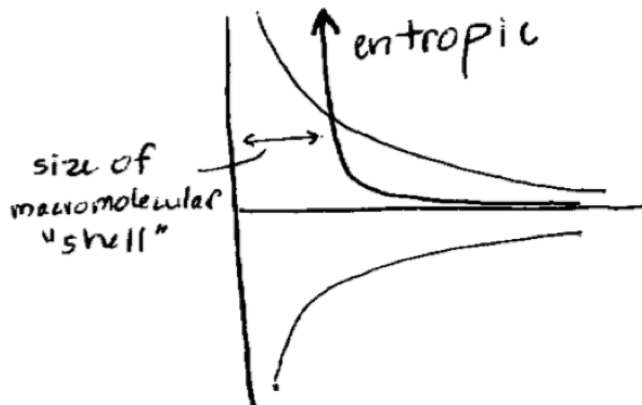
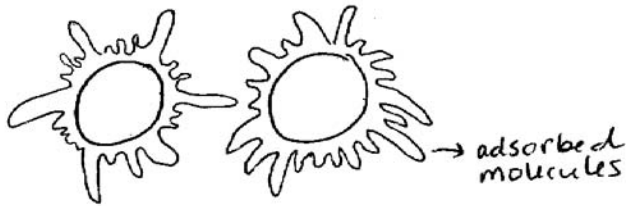
- high  $\zeta$  potential  $\Rightarrow$  well separated particles in suspension  $\Rightarrow$  uniform packing when settled  $\Rightarrow$  sinters to a regular structure with uniform grains

Date: May 14th, 2012.

- **low  $\zeta$  potential**  $\Rightarrow$  particles agglomerate in suspension  $\Rightarrow$  aggregates settle  $\Rightarrow$  larger voids, irregular structure in sintered body
- **settling**  $\Rightarrow$  lower velocity settling  $\Rightarrow$  spend more time going over the “repulsive hill”  $\Rightarrow$  less flocculation, more uniform settling
- **slip casting**  $\Rightarrow$  higher velocity settling  $\Rightarrow$  spend less time going over the “repulsive hill” and enter the flocculation minimum  $\Rightarrow$  more flocculation, less uniform settling

### Add Macromolecules

$$U = H - TS$$



$\Rightarrow$  adsorbed macromolecules add entropic repulsion effects

### Vacuum/Vapor Deposition Processes

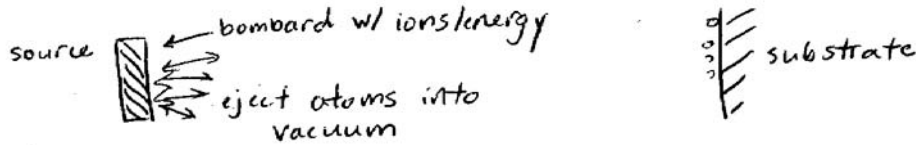
- semiconductor devices, integrated circuits, MEMS, etc.
- coatings for decoration (furniture, sports equipment, faucetry) or abrasion resistance (cutting/machining, tooling, blades)

Two main classes of processes

| <u>PVD</u><br>physical vapor deposition  | <u>CVD</u><br>chemical vapor deposition   |
|--|---|
| vacuum process (low pressure)<br>solid or liquid source<br>no chemical reaction, just adsorption<br>geometry dominated | vapor process (high pressure)<br>gas source<br>chemical reactions occur<br>fluid flow and diffusion dominated |

**PVD**

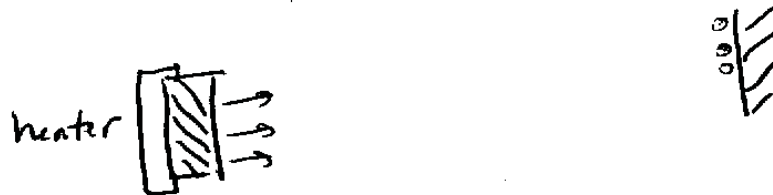
1. sputtering



2. e-beam

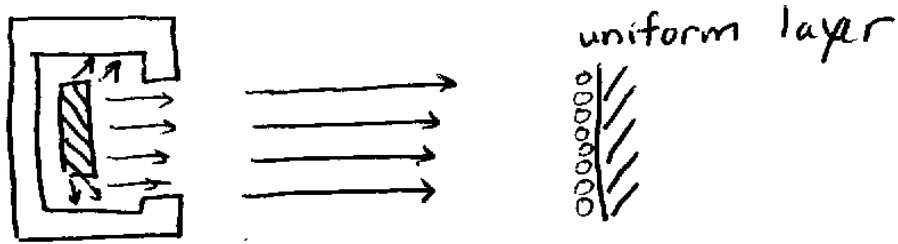


3. evaporation



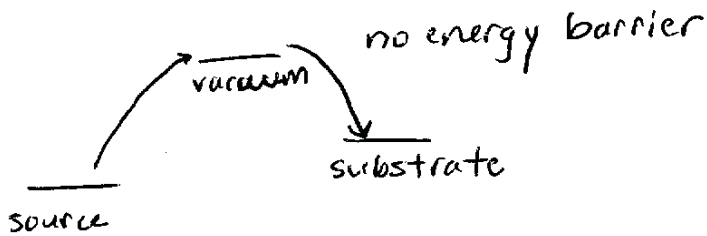
4. pulsed laser deposition

## 5. MBE - molecular beam epitaxy



## 6. plasma enhanced deposition

PVD Energy Diagram:



**no chemical reaction:** the deposition rate is as fast as atoms are supplied

⇒ geometry dominated, source limited

⇒  $s \propto t \propto$  supplied flux,  $J \frac{\text{mol}}{\text{m}^2\text{s}}$

⇒  $\frac{ds}{dt} = J \cdot V_m$ , where  $V_m$  is molar volume, geometry factor

e.g. **Evaporation**

$$J = \frac{P_e - P}{\sqrt{2\pi MwRT}}$$

where  $P_e$  is equilibrium vapor pressure,  $P$  is pressure  $\approx 0$  (vacuum), and  $Mw$  is molecular weight

Next time: **CVD**

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<http://ocw.mit.edu>

3.044 Materials Processing  
Spring 2013

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